

Abstract Submitted
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Fabrication of Bismuth Selenide Topological Insulating Samples LUCAS ORONA, HADAR STEINBERG, VALLA FATEMI, FERHAT KATMIS, JAGADEESH MOODERA, PABLO JARILLO-HERRERO, MIT — In this talk, I will discuss fabrication of nanometric topological insulator Bi_2Se_3 devices. Our group uses two fabrication methodologies: Epitaxial thin films and single crystal exfoliation. I will discuss the benefits and drawbacks of each methodology. I will also address the effects on device performance by various steps of the fabrication process.

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